MUEGGE

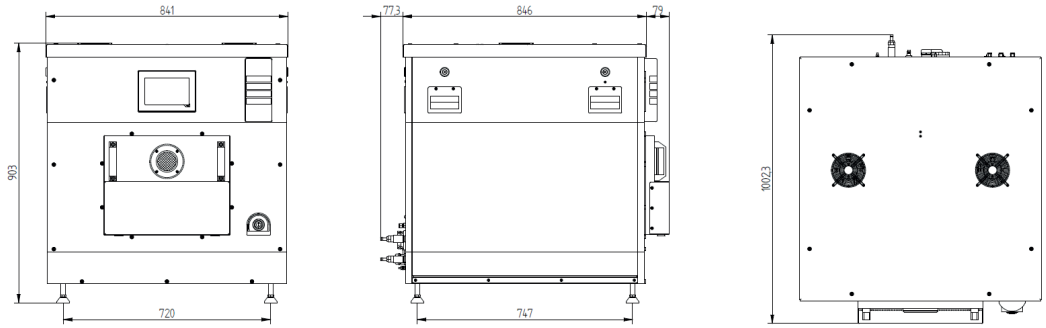
MW-PLASMA SYSTEM MA1250D-121BB

STRIPPING TOOL

Features

- Optimized for the removal of thick photoresist layers (e.g. SU-8, KMPR, etc.)
- Very high selectivity to Si and Si compounds like SiO2 or Si3N4
- Unique design for isotropic etching of materials such as Si, SiO2, SiN, SiOxNy, W, Mo, etc.
- Pure chemical etching without attack of the substrate by ions
- Integrated compact RPS (Remote Plasma Source)
- Water cooled plasma zone
- Very low thermal load of the substrates
- Substrate size up to 240 mm x 240 mm
- No attack of metals (Ni, Ni/Fe, Au, Cu, etc.)
- High environmental compatibility
- For 1 x 8“ or 1 x 6“ or 2 x 4“ wafers

Outline Dimensions (mm)



MUEGGE GmbH · Hochstr. 4–6 · 64385 Reichelsheim/Germany · Phone: (+49) 6164 9307-0 · info@muegge.de · www.muegge-group.com

MUEGGE

Specifications

Mains voltage	3~ (L1 / L2 / L3 / PE) 400 V, 8,5 A, 50 / 60 Hz
Mains leakage current	< 10,5 mA @ 520 V / 50 Hz
HF output	1000 W
Cooling	Air / Water ≥ 5 (1,32) l/min (US.gal/min) 4 - 6 (58,02 - 87,02) bar (psi) @ 20 - 25 (68 - 77) °C (°F)
Process gases	O2, CF4, N2, -, -, -
Vacuum connection	KF-40

Dimensions	Width: 841 (33,11) mm (inch) Height: 903 (35,55) mm (inch) Depth: 1003 (39,48) mm (inch)
Size of working plate	245 x 245 (9.65 x 9.65) mm (inch)
Conditions	In operation: 5 °C (41 °F) - 40 °C (104 °F), relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing, 3K3 Storage: - 25 °C (- 13 °F) to + 70 °C (158 °F), 70 kPa - 106 kPa, relative humidity 80 % to 30 °C (86 °F), above this linearly reduced to 50 %, non-condensing, 1K3
Frequency	2450 MHz
Compressed air	6 - 9 (87,02 - 130,53) bar (psi) Oil free, dry, 5 µm filtered
Weight	298 (656,98) kg (lbs)

Recommended system components

- Vacuum pump (dry pump min. 300 m^3/h)
- Gas cleaning system (CS CLEAN dry absorber)